NSN 5961-01-027-9696

Yes - demil/mli

Fiig: A110a0

Photo Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-027-9696 **Inclosure Material:** Plastic **Overall Length:** 0.102 inches **Overall Diameter:** 0.060 inches **Function For Which Designed:** Phototransistor **Mounting Method:** Press fit **Semiconductor Material:** Gallium arsenide **Voltage Rating In Volts Per Characteristic:** 15.0 breakdown voltage, collector-to-emitter, base open and 5.0 breakdown voltage, emitter to collector, base open **Current Rating Per Characteristic:** 7.00 milliamperes operating voltage absolute and 21.00 milliamperes zero-gate-voltage source current absolute **Maximum Operating Tempurature Per Measurement Point:** 70.0 degrees celsius ambient air **Terminal Type And Quantity:** 2 tab, solder lug and 1 case Shelf Life: N/a **Unit Of Measure: Demilitarization:**